

FRAM

MB85R256G

MB85R256G is a 256K-bits FRAM LSI using the ferroelectric process and CMOS process technologies for forming the nonvolatile memory cells. Because FRAM is able to write high-speed even though a nonvolatile memory, it is suitable for the log management and the storage of the resume data, etc. MB85R256G uses a pseudo-SRAM interface compatible with conventional asynchronous SRAM.

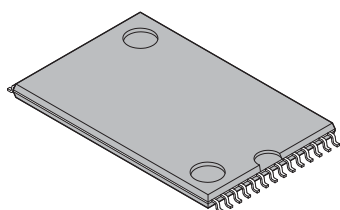
■ FEATURES

- **Bit configuration** : 32,768 words × 8 bits
- **Read/write endurance** : 10¹⁰ times/bit
- **Peripheral circuit CMOS construction**
- **Operating power supply voltage** : 2.7 to 3.6V
- **Operating temperature range** : -40°C to +85°C
- **Data retention** : 10 years (+70°C)
- **Package** : 28-pins, SOP flat package
: 28-pins, TSOP(1) flat package

■ ORDERING INFORMATION

Product name	Package	Remarks
TBD	Plastic • SOP, 28-pins (FPT-28P-M17) 8.60mm×17.75mm, 1.27mm pitch	-
TBD	Plastic • TSOP, 28-pins (FPT-28P-M19) 11.80mm×8.00mm, 0.55mm pitch	-
TBD	Plastic • SOP, 28-pins (FPT-28P-M17) 8.60mm×17.75mm, 1.27mm pitch	Embossed Carrier tape

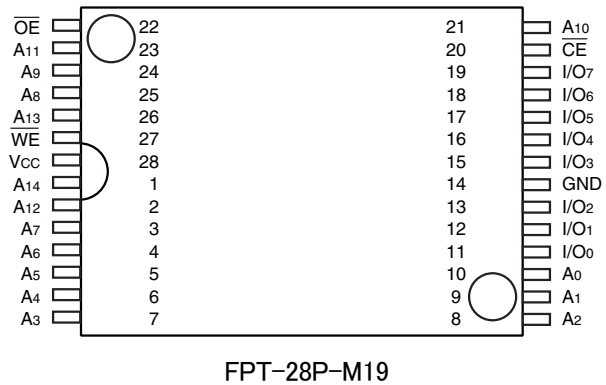
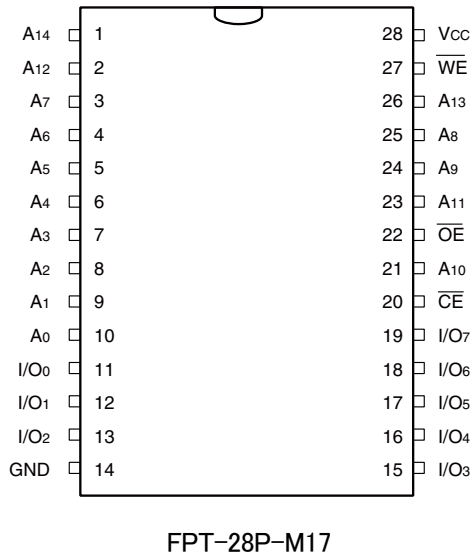
■ PACKAGE EXAMPLE OF REFERENCE



Plastic • TSOP, 28-pins
(FPT-28P-M19)

■ PIN ASSIGNMENT

(TOP VIEW)



Pin No.	Pin name	Description
1 to 10, 21, 23 to 26	A ₀ to A ₁₄	Address input
11 to 13, 15 to 19	I/O ₀ to I/O ₇	Data input/output
20	\overline{CE}	Chip enable input
27	\overline{WE}	Write enable input
22	\overline{OE}	Output enable input
28	V _{CC}	Power supply (+3.3V Typ.)
14	GND	Ground

■ BLOCK DIAGRAM
